



#### 80V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
001/	17mΩ @ V <sub>GS</sub> = 10V	44A
80V	$22m\Omega$ @ $V_{GS} = 4.5V$	38A

### **Features**

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

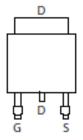
### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 63
- Weight: 0.33 grams (Approximate)

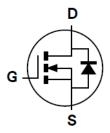




Top View



Pin Out Top View



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

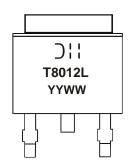
Part Number	Case	Packaging
DMT8012LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) complaint. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

TO252 (DPAK)



T8012L = Product Type Marking
T8012L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	80	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	44 28	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	80	Α
Maximum Continuous Body Diode Forward Current (Note 5)		I <sub>S</sub>	3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	80	Α
Avalanche Current, L=0.1mH		I <sub>AS</sub>	11.6	Α
Avalanche Energy, L=0.1mH		E <sub>AS</sub>	10.2	mJ

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	50	W
Thermal Resistance, Junction to Case (Note 6)	Rejc	2.5	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

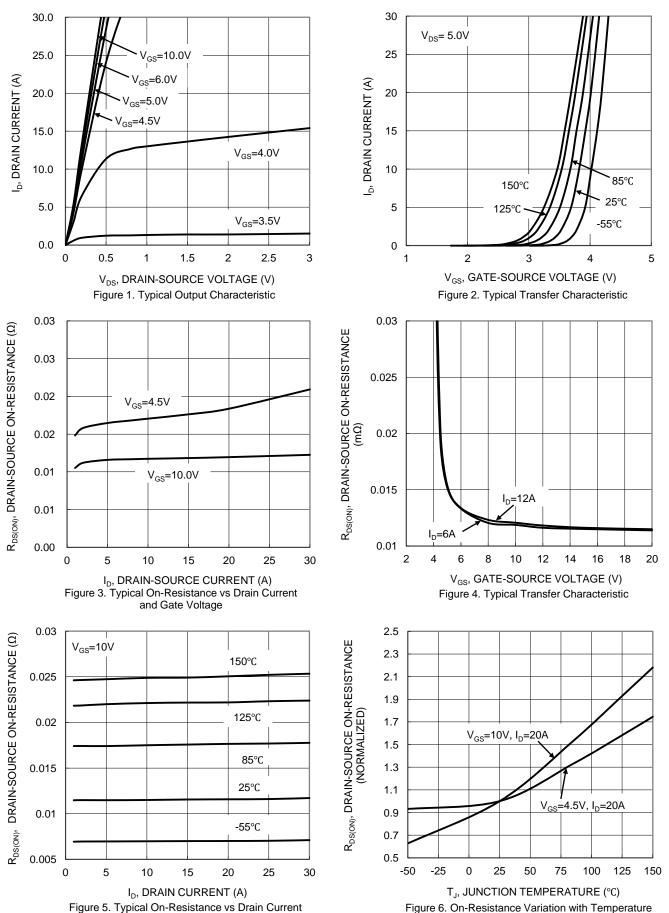
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
DFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	-	-	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	12	17	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>		18.2	22		$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	$V_{SD}$	-	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 25A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	1,949	-		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	-	177	-	pF		
Reverse Transfer Capacitance	Crss	-	10	-			
Gate Resistance	Rg	-	0.7	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	15	-		V <sub>DS</sub> = 40V, I <sub>D</sub> = 12A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	34	-	nC		
Gate-Source Charge	$Q_{gs}$	-	6	-	IIC		
Gate-Drain Charge	$Q_{gd}$	-	4.5	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.9	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	-	3.8	-			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	16.5	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	3.5	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	30.2	-	ns I to a little toolate		
Body Diode Reverse Recovery Charge	Qrr	-	34.6	-	nC	$I_F = 12A$ , di/dt = 100A/ $\mu$ s	

<sup>5.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.6. Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

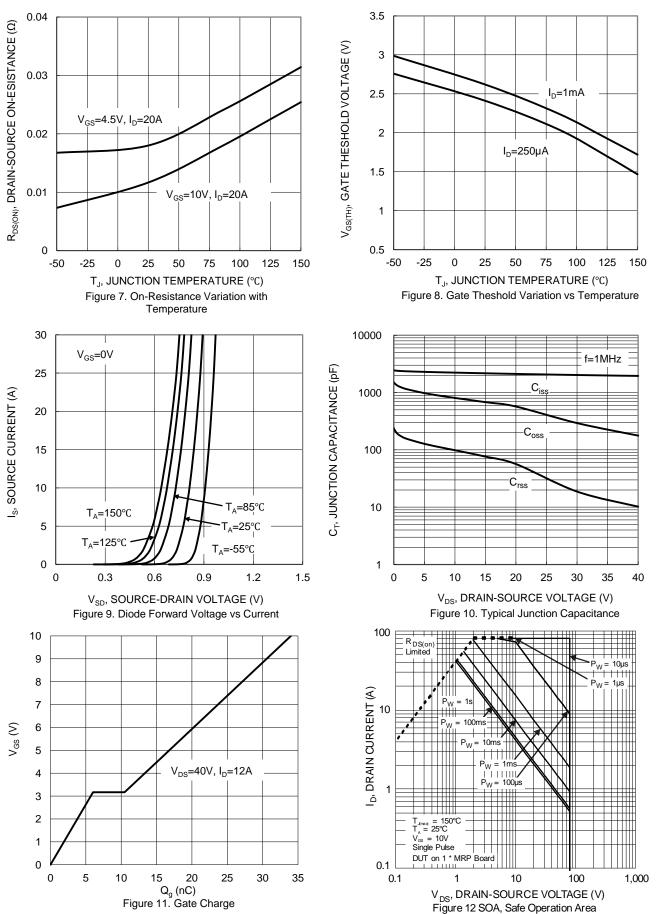
<sup>8.</sup> Guaranteed by design. Not subject to product testing.



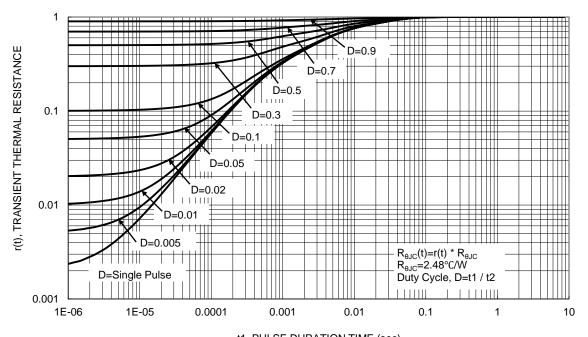


and Temperature







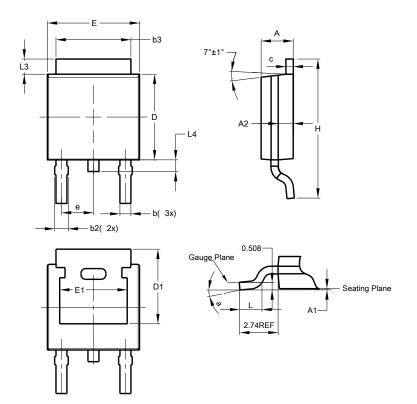


t1, PULSE DURATION TIME (sec) Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

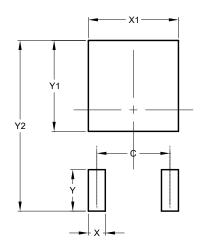
Please see http://www.diodes.com/package-outlines.html for the latest version.



TOOSO (DDAI()						
TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
<b>A1</b>	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	ı			
Η	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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